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Exhibitor Introduction	TES Co., Ltd. is a Korea-based semiconductor equipment company specializing in CVD and high-temperature MOCVD systems. Based on its accumulated experience in front-end semiconductor CVD equipment, TES is expanding its compound semiconductor business for wide-bandgap devices. The company focuses on Power SiC for EVs, high-voltage power grids, renewable energy, ESS, rail and AI data-center power infrastructure, and RF GaN on SiC for 5G/6G, LEO satellite communication, radar and defense applications. TES develops production-oriented epitaxy platforms that address key requirements such as high-temperature stability, high growth rate, process uniformity, low defect density and scalable system architecture. TES also supports customer-specific Ga2O3 epitaxy development.	
Exhibit Product	TES will exhibit TRION, a tunable high-temperature epitaxy platform for Power SiC and RF GaN HEMT on SiC. For Power SiC, TRION SiC targets thin re-growth epi, MOSFET drift layers and thick high-voltage epi, with high growth rate and excellent thickness and doping uniformity. For RF GaN, TRION GaN enables high-quality thick AlN buffer growth on SiC using high-temperature operation, fast gas switching and pulsed growth to improve crystallinity, insulation and thermal performance. TRION combines a special pancake-type RF T-Heater and a tunable triple-pair nozzle, allowing spatial control of temperature and gas distribution. This tunable architecture supports uniformity control, process recovery and scale-up without changing the core platform.	